100 V, 1 A NPN low VCEsat transistor

28 September 2023

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110T

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}

3. Applications

- Major application segments
 - Automotive 42 V power
 - Telecom infrastructure
 - Industrial
- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - · LCD backlighting
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	165	200	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В
				 E
			1	sym123
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number Package							
	Name	Description	Version				
PBSS8110T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS8110T	%U8

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	120	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

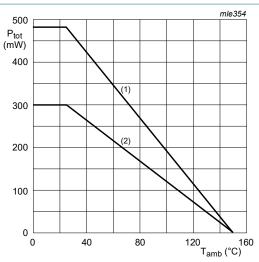
Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

PBSS8110T

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- (1) FR4 PCB; 1 cm² copper mounting pad for collector.
- (2) Standard footprint.

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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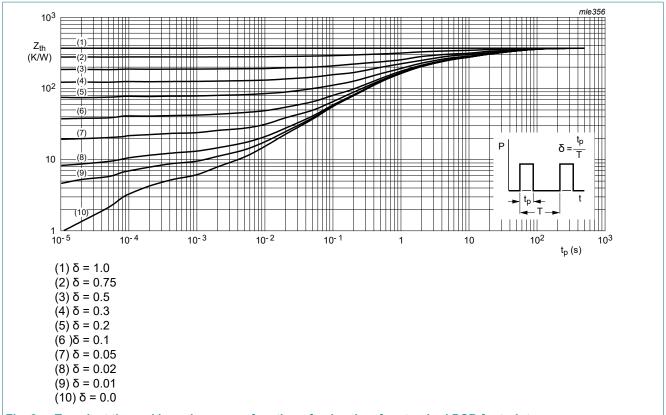
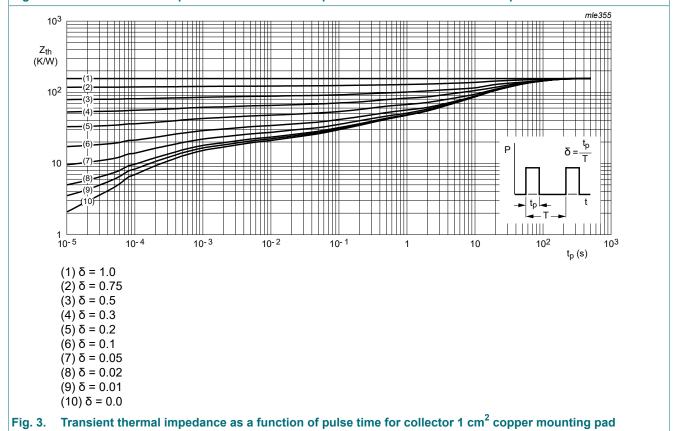


Fig. 2. Transient thermal impedance as a function of pulse time for standard PCB footprint



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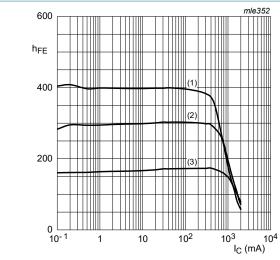
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	120	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_{C} = 10 mA; I_{B} = 0 A; pulsed; t_{p} ≤ 300 µs; δ ≤ 0.02;; T_{amb} = 25 °C	100	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = 100 \ \mu\text{A}; \ I_C = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 1 mA; T _{amb} = 25 °C	150	-	-	
		V _{CE} = 10 V; I _C = 250 mA; T _{amb} = 25 °C	150	-	500	
		V_{CE} = 10 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	-	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	80	-	-	
CEsat collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	-	-	40	mV	
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	120	mV
		$I_C = 1 \text{ A}$; $I_B = 100 \text{ mA}$; pulsed; $t_p \le$	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	165	200	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; T _{amb} = 25 °C	-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 10 V; I _C = 1 A; T _{amb} = 25 °C	-	-	0.9	V
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	-	7.5	pF

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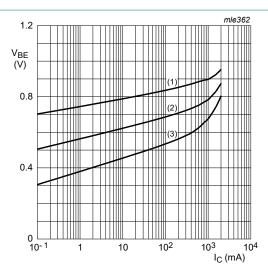


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values

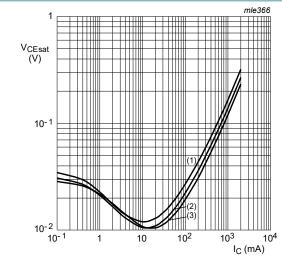


$$V_{CF} = 10 \text{ V}$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



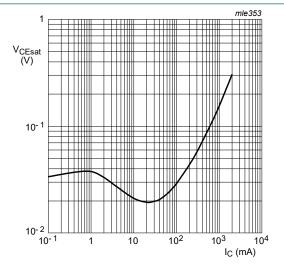
$$I_C/I_B = 10$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Collector-emitter saturation voltage as a Fig. 6. function of collector current; typical values



$$I_C/I_B = 20$$

 $T_{amb} = 25 °C$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

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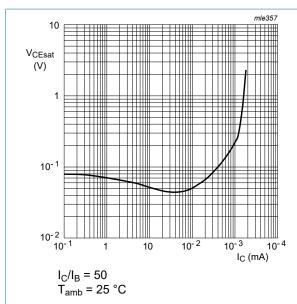


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

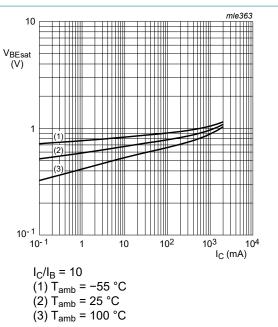
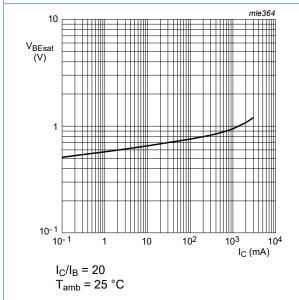


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



collector current; typical values

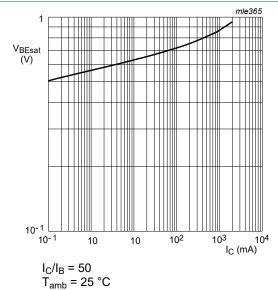
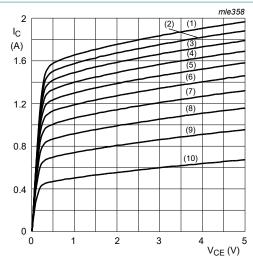


Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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T_{amb} = 25 °C

(1) $I_B = 35.0 \text{ mA}$

(2) $I_B = 31.5 \text{ mA}$

 $(3) I_B = 28.0 \text{ mA}$

 $(4) I_B = 24.5 \text{ mA}$

 $(5) I_B = 21.0 mA$

(6) $I_B = 17.5 \text{ mA}$ $(7) I_B = 14.0 \text{ mA}$

 $(8) I_B = 10.5 \text{ mA}$

(9) $I_B = 7.0 \text{ mA}$ $(10) I_B = 3.5 \text{ mA}$

Fig. 12. Collector current as a function of collectoremitter voltage; typical values

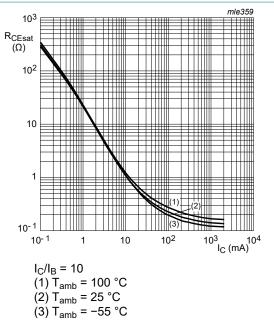


Fig. 13. Collector-emitter equivalent on-resistance as a function of collector current; typical values

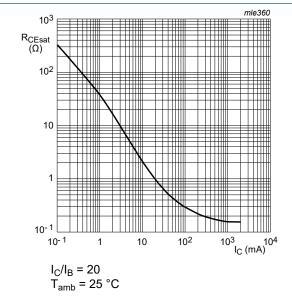


Fig. 14. Collector-emitter equivalent on-resistance as a function of collector current; typical values

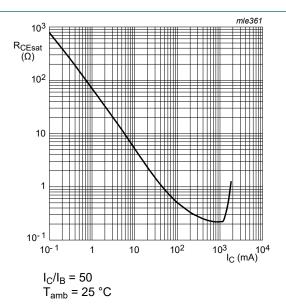
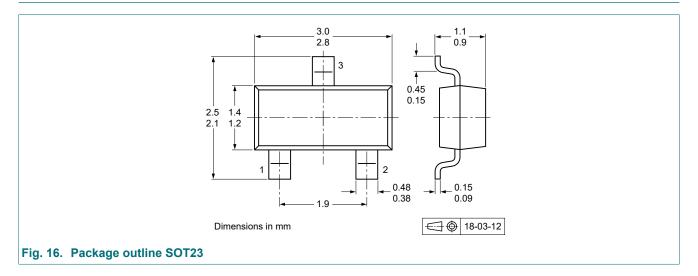


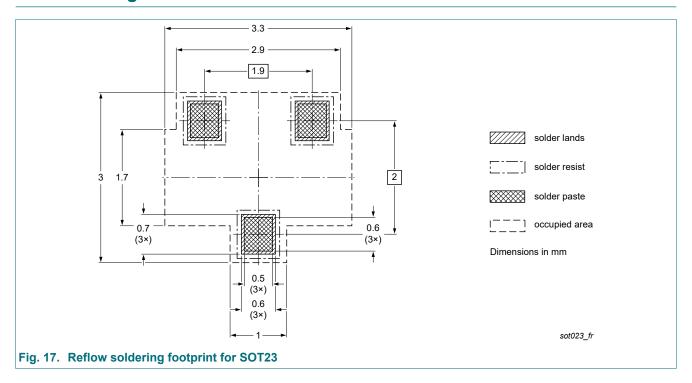
Fig. 15. Collector-emitter equivalent on-resistance as a function of collector current; typical values

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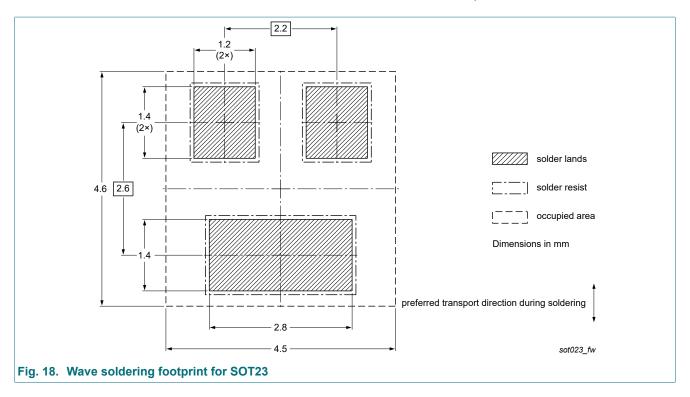
11. Package outline



12. Soldering



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13. Revision history

Table 8. Revision history

Table of Revision metery							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS8110T v.5	20230928	Product data sheet	-	PBSS8110T v.4			
Modifications:	Characteristics.	, Fig. 12: Values of curves ar	re corrected				
PBSS8110T v.4	20230101	Product data sheet	-	PBSS8110T v.3			
PBSS8110T v.3	20220513	Product data sheet	-	PBSS8110T v.2			
PBSS8110T v.2	20031222	Product data sheet	-	PBSS8110T v.1			
PBSS8110T v.1	20030728	Product data sheet	-	-			

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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